

BTA202X series D and E

2 A Three-quadrant triacs high commutation

Rev. 01 — 7 February 2008

Product data sheet

1. Product profile

1.1 General description

Passivated high commutation triacs in a SOT186A 'full pack' plastic package. These triacs balance the requirements of commutation performance and gate sensitivity. The 'sensitive' gate E series and 'logic level' D series are intended for interfacing with low-power drivers, including microcontrollers.

1.2 Features

- Sensitive gate
- Very high commutation performance maximized at each gate sensitivity
- High immunity to dV/dt
- High isolation voltage

1.3 Applications

- Motor control
- Solenoid driver

1.4 Quick reference data

- $V_{\text{DRM}} \leq 600 \text{ V}$ (BTA202X-600D)
- $V_{\text{DRM}} \leq 600 \text{ V}$ (BTA202X-600E)
- $V_{\text{DRM}} \leq 800 \text{ V}$ (BTA202X-800D)
- $V_{\text{DRM}} \leq 800 \text{ V}$ (BTA202X-800E)
- $I_{\text{T(RMS)}} \leq 2 \text{ A}$
- $I_{\text{GT}} \leq 5 \text{ mA}$ (BTA202X-600D)
- $I_{\text{GT}} \leq 10 \text{ mA}$ (BTA202X-600E)
- $I_{\text{GT}} \leq 5 \text{ mA}$ (BTA202X-800D)
- $I_{\text{GT}} \leq 10 \text{ mA}$ (BTA202X-800E)

2. Pinning information

Table 1. Pinning

Pin	Description	Simplified outline	Graphic symbol
1	main terminal 1 (T1)		
2	main terminal 2 (T2)		
3	gate (G)		
mb	mounting base (isolated)		

SOT186A (TO-220F)

3. Ordering information

Table 2. Ordering information

Type number	Package		Version
	Name	Description	
BTA202X-600D	TO-220F	plastic single-ended package; isolated heatsink mounted; 1 mounting hole; 3-lead TO-220 'full pack'	SOT186A
BTA202X-600E			
BTA202X-800D			
BTA202X-800E			

4. Limiting values

Table 3. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DRM}	repetitive peak off-state voltage	BTA202X-600D; BTA202X-600E	[1]	600	V
		BTA202X-800D; BTA202X-800E		800	V
$I_{T(RMS)}$	RMS on-state current	full sine wave; $T_h \leq 110\text{ °C}$; see Figure 4 and 5	-	2	A
I_{TSM}	non-repetitive peak on-state current	full sine wave; $T_j = 25\text{ °C}$ prior to surge; see Figure 2 and 3			
		$t = 20\text{ ms}$	-	14	A
		$t = 16.7\text{ ms}$	-	15.4	A
I^2t	I^2t for fusing	$t_p = 10\text{ ms}$	-	0.98	A ² s
dl_T/dt	rate of rise of on-state current	$I_{TM} = 1.5\text{ A}$; $I_G = 0.2\text{ A}$; $dl_G/dt = 0.2\text{ A}/\mu\text{s}$	-	100	A/ μs
I_{GM}	peak gate current		-	2	A
P_{GM}	peak gate power		-	5	W

Table 3. Limiting values ...continued

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$P_{G(AV)}$	average gate power	over any 20 ms period	-	0.5	W
T_{stg}	storage temperature		-40	+150	°C
T_j	junction temperature		-	125	°C

[1] Although not recommended, off-state voltages up to 800 V may be applied without damage, but the triac may switch to the on-state. The rate of rise of current should not exceed 6 A/μs.

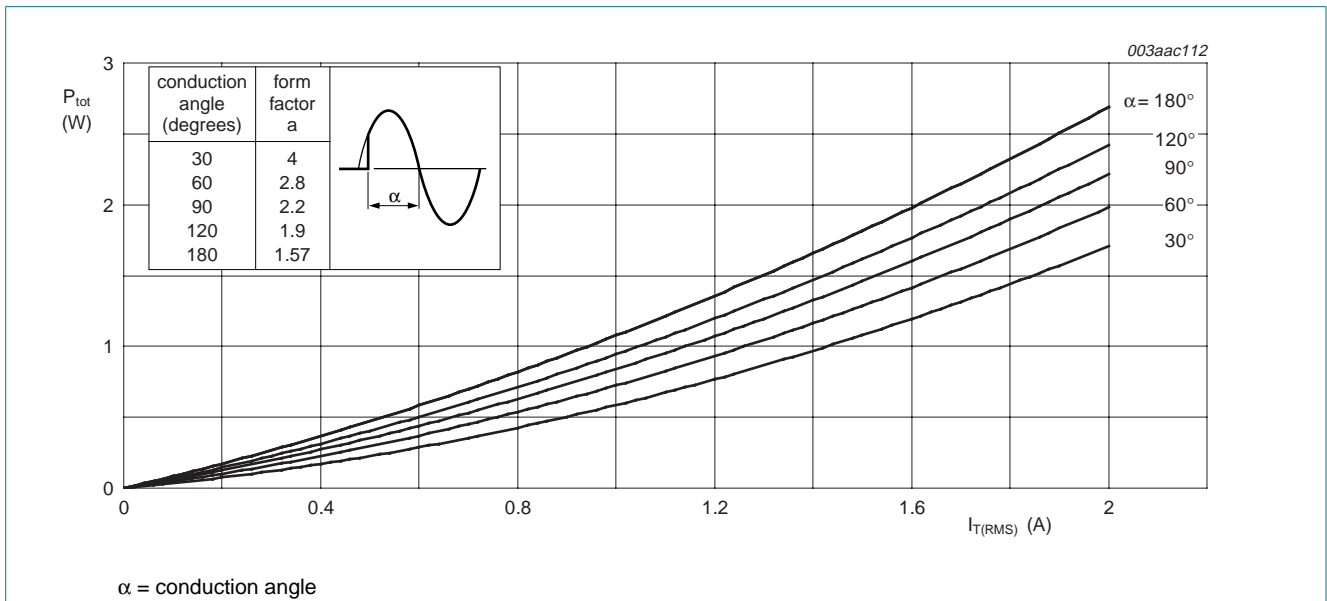


Fig 1. Total power dissipation as a function of RMS on-state current; maximum values

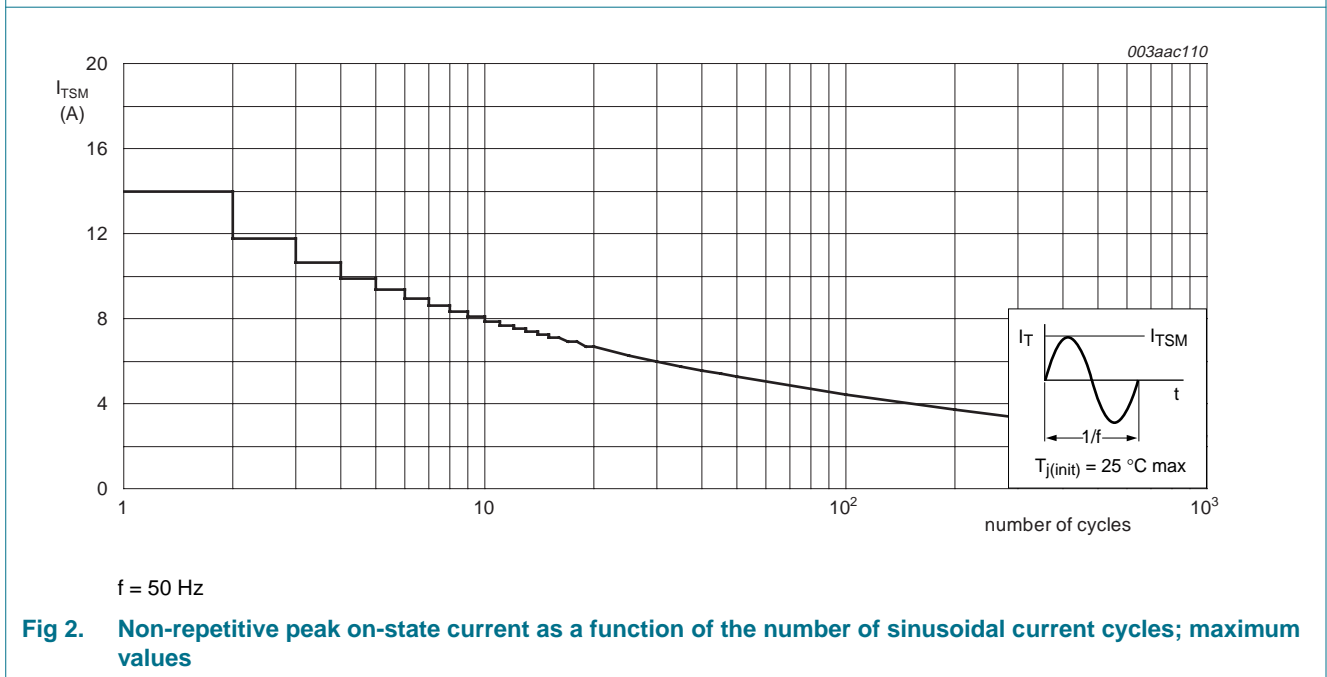
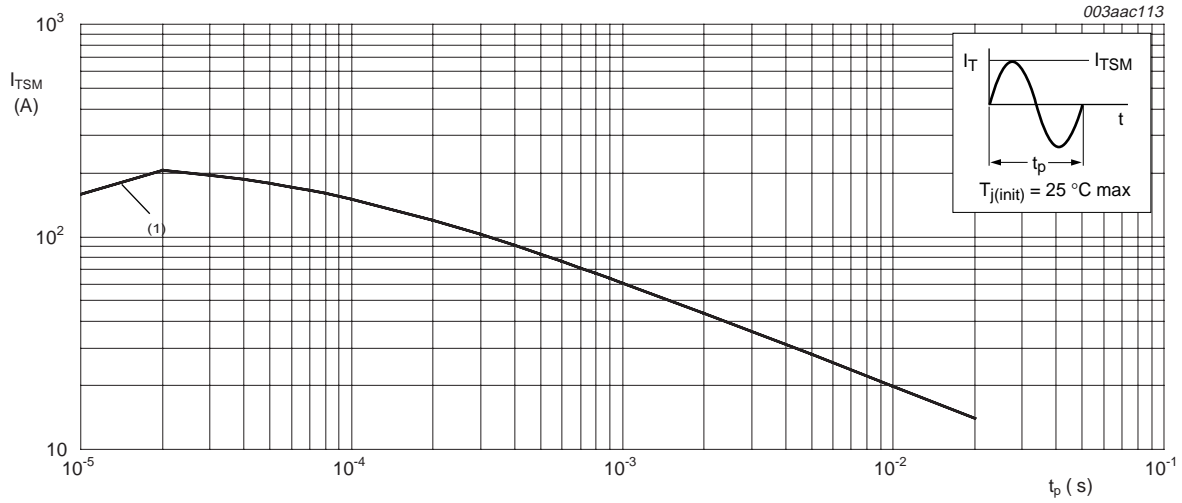
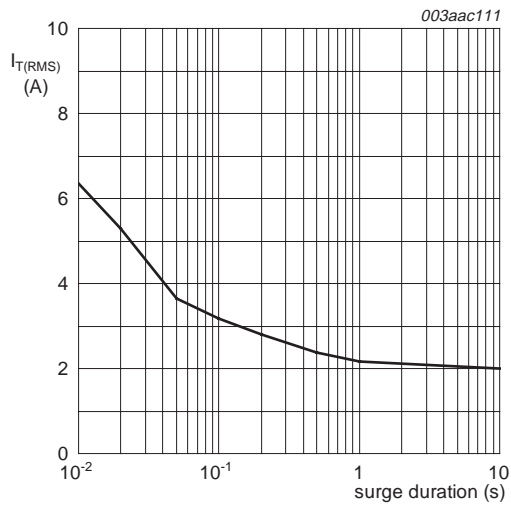


Fig 2. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values



$t_p \leq 20\text{ ms}$
(1) di_T/dt limit

Fig 3. Non-repetitive peak on-state current as a function of pulse width; maximum values



$f = 50\text{ Hz}; T_h = 110\text{ °C}$

Fig 4. RMS on-state current as a function of surge duration; maximum values

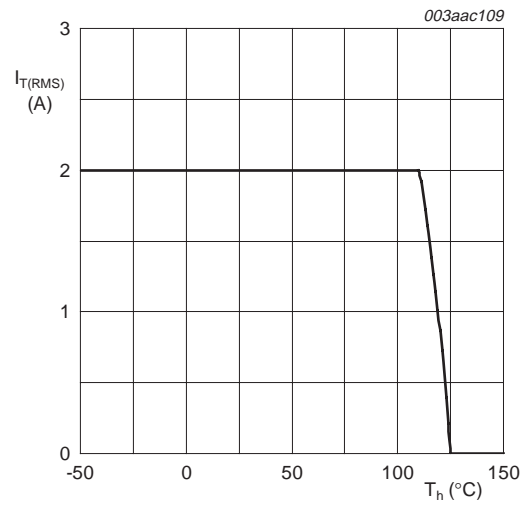


Fig 5. RMS on-state current as a function of heatsink temperature; maximum values

5. Thermal characteristics

Table 4. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-h)}$	thermal resistance from junction to heatsink	bidirectional; see Figure 6	-	-	5.5	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	-	55	-	K/W

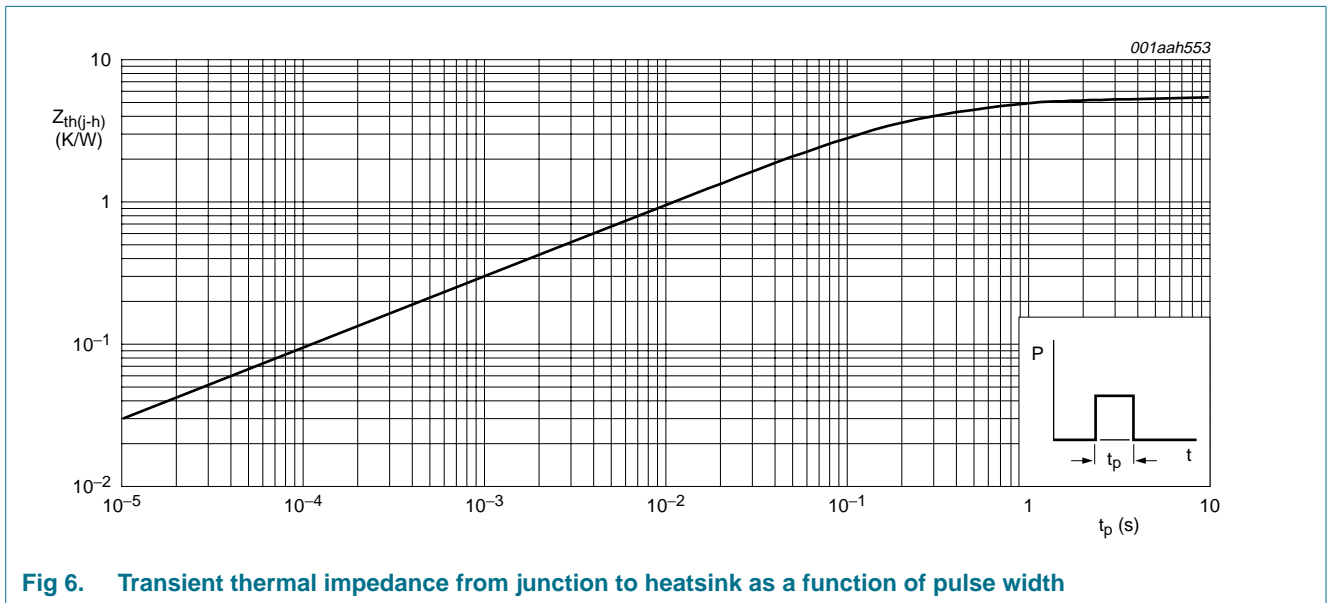


Fig 6. Transient thermal impedance from junction to heatsink as a function of pulse width

6. Isolation characteristics

Table 5. Isolation limiting values and characteristics

$T_h = 25^\circ\text{C}$ unless otherwise specified.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{isol(RMS)}$	RMS isolation voltage	from all three terminals to external heatsink; $f = 50\text{ Hz to }60\text{ Hz}$; sinusoidal waveform; $RH \leq 65\%$; clean and dust free	-	-	2500	V
C_{isol}	isolation capacitance	from pin 2 to external heatsink; $f = 1\text{ MHz}$	-	10	-	pF

7. Static characteristics

Table 6. Static characteristics

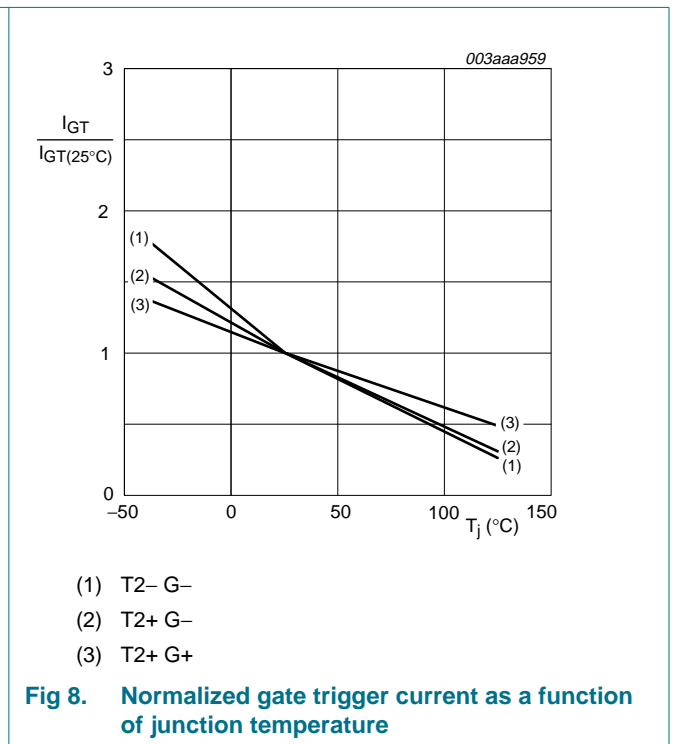
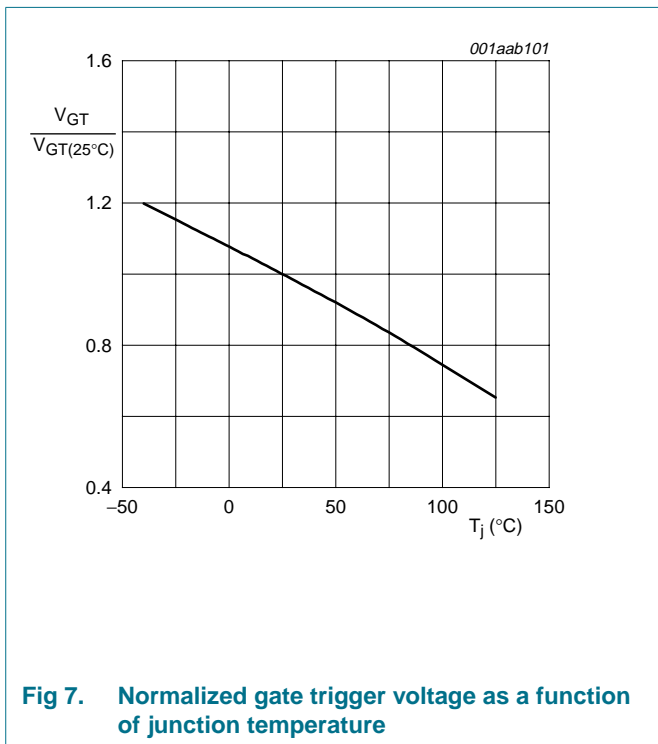
$T_j = 25\text{ °C}$ unless otherwise specified.

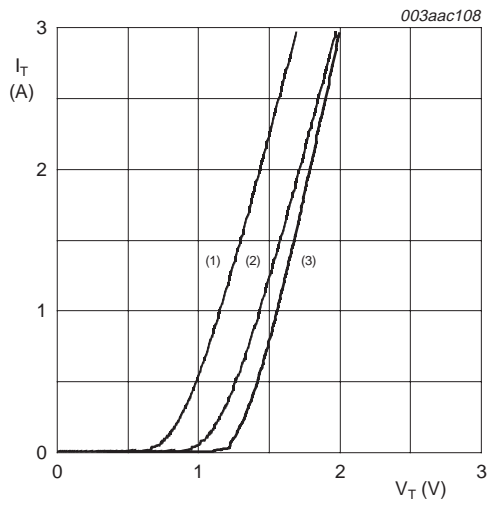
Symbol	Parameter	Conditions	BTA202X-600D BTA202X-800D			BTA202X-600E BTA202X-800E			Unit
			Min	Typ	Max	Min	Typ	Max	
I_{GT}	gate trigger current	$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; see Figure 8							
		T2+ G+	0.25	-	5	0.5	-	10	mA
		T2+ G-	0.25	-	5	0.5	-	10	mA
		T2- G-	0.25	-	5	0.5	-	10	mA
I_L	latching current	$V_D = 12\text{ V}$; $I_{GT} = 0.1\text{ A}$; see Figure 10							
		T2+ G+	-	-	5	-	-	12	mA
		T2+ G-	-	-	10	-	-	20	mA
		T2- G-	-	-	5	-	-	12	mA
I_H	holding current	$V_D = 12\text{ V}$; $I_{GT} = 0.1\text{ A}$; see Figure 11	-	-	5	-	-	12	mA
V_T	on-state voltage	$I_T = 3\text{ A}$; see Figure 9	-	1.63	2	-	1.63	2	V
V_{GT}	gate trigger voltage	$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; see Figure 7	-	0.7	1.5	-	0.7	1.5	V
		$V_D = 400\text{ V}$; $I_T = 0.1\text{ A}$; $T_j = 125\text{ °C}$	0.2	0.3	-	0.2	0.3	-	V
I_D	off-state current	$V_D = V_{DRM(max)}$; $T_j = 125\text{ °C}$	-	0.1	0.5	-	0.1	0.5	mA

8. Dynamic characteristics

Table 7. Dynamic characteristics

Symbol	Parameter	Conditions	BTA202X-600D BTA202X-800D			BTA202X-600E BTA202X-800E			Unit
			Min	Typ	Max	Min	Typ	Max	
dV_D/dt	rate of rise of off-state voltage	$V_{DM} = 0.67 \times V_{DRM(max)}$; $T_j = 125\text{ }^\circ\text{C}$; exponential waveform; $R_{(G-MT1)} = 220\ \Omega$	-	350	-	-	500	-	V/ μs
dl_{com}/dt	rate of change of commutating current	$V_{DM} = 400\text{ V}$; $T_j = 125\text{ }^\circ\text{C}$; $I_{T(RMS)} = 2\text{ A}$; $dV_{com}/dt = 20\text{ V}/\mu\text{s}$; gate open circuit	1.0	-	-	2.0	-	-	A/ms
		$V_{DM} = 400\text{ V}$; $T_j = 125\text{ }^\circ\text{C}$; $I_{T(RMS)} = 2\text{ A}$; $dV_{com}/dt = 10\text{ V}/\mu\text{s}$; gate open circuit	1.2	-	-	2.3	-	-	A/ms
t_{gt}	gate-controlled turn-on time	$I_{TM} = 20\text{ A}$; $V_D = V_{DRM(max)}$; $I_G = 0.1\text{ A}$; $dl_G/dt = 5\text{ A}/\mu\text{s}$	-	2	-	-	2	-	μs





- $V_o = 0.9\text{ V}$
 $R_s = 0.267\ \Omega$
- (1) $T_j = 125^\circ\text{C}$; typical values
 - (2) $T_j = 125^\circ\text{C}$; maximum values
 - (3) $T_j = 25^\circ\text{C}$; maximum values

Fig 9. On-state current as a function of on-state voltage

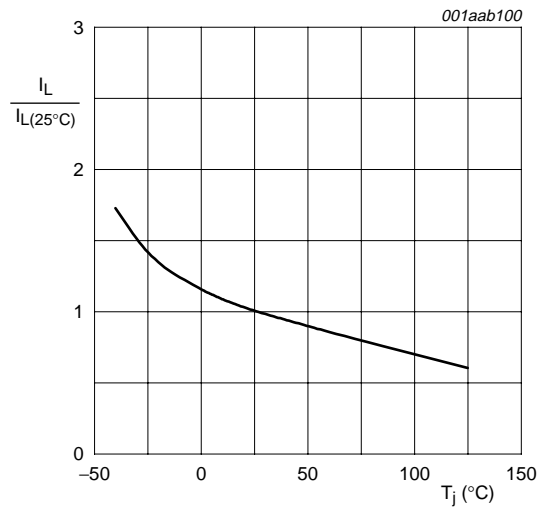


Fig 10. Normalized latching current as a function of junction temperature

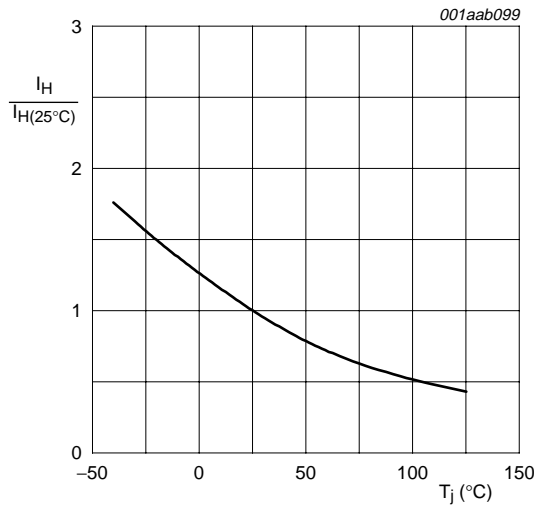


Fig 11. Normalized holding current as a function of junction temperature

9. Package information

Refer to mounting instructions for F-pack packages.

Epoxy meets UL94 V-0 at 3.175 mm.

10. Package outline

Plastic single-ended package; isolated heatsink mounted;
1 mounting hole; 3-lead TO-220 'full pack'

SOT186A

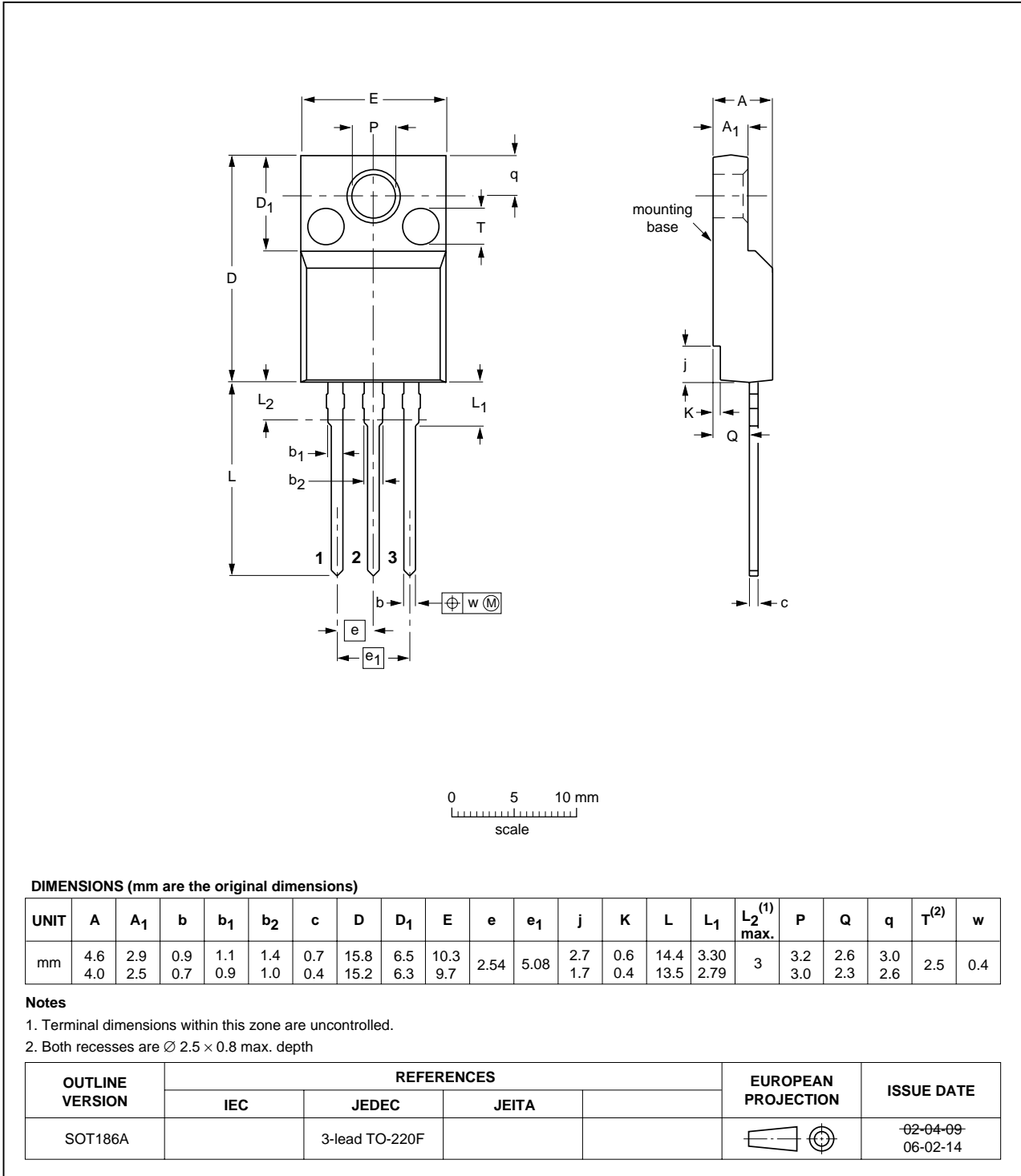


Fig 12. Package outline SOT186A (3-lead TO-220F)

11. Revision history

Table 8. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BTA202X_SER_D_E_1	20080207	Product data sheet	-	-

12. Legal information

12.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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